

N-channel 800 V, 0.37 Ω , 12 A Zener-protected SuperMESH™ 5
Power MOSFET in D²PAK, TO-220FP and TO-220 packages

Datasheet - production data

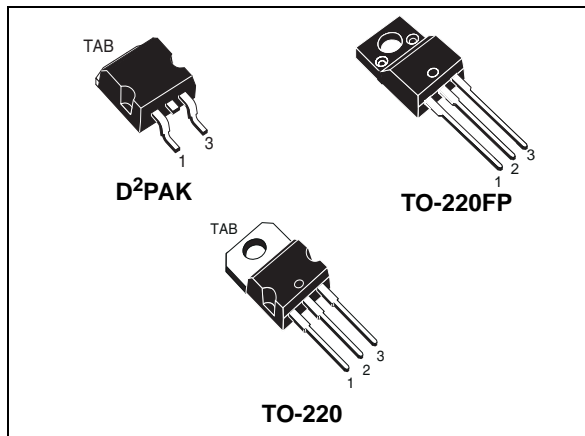
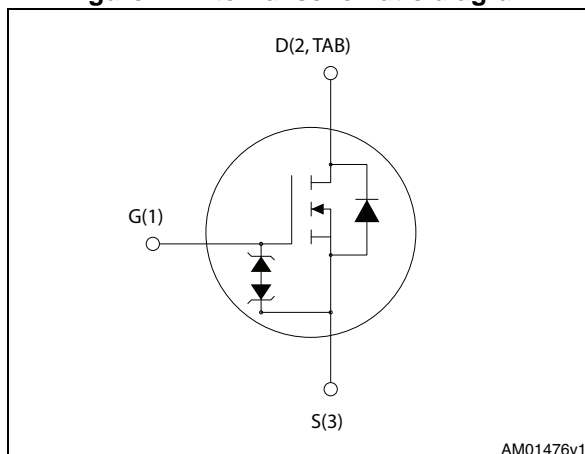


Figure 1. Internal schematic diagram



Features

Order codes	V _{DSS}	R _{DS(on)}	I _D	P _{TOT}
STB13N80K5	800 V	< 0.45 Ω	12 A	190 W
STF13N80K5	800 V	< 0.45 Ω	12 A	35 W
STP13N80K5	800 V	< 0.45 Ω	12 A	190 W

- Worldwide best FOM (figure of merit)
- Ultra low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Zener-protected Power MOSFETs realized in SuperMESH™ 5, a revolutionary avalanche-rugged very high voltage Power MOSFET technology based on an innovative proprietary vertical structure. The result is a drastic reduction in on-resistance and ultra low gate charge for applications which require superior power density and high efficiency.

Table 1. Device summary

Order codes	Marking	Packages	Packaging
STB13N80K5	13N80K5	D ² PAK	Tape and reel
STF13N80K5	13N80K5	TO-220FP	Tube
STP13N80K5	13N80K5	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		D ² PAK, TO-220	TO-220FP	
V _{GS}	Gate-source voltage	± 30		V
I _D	Drain current (continuous) at T _C = 25 °C	12	12 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	7.6	7.6 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	48	48 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	190	35	W
I _{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T _{jmax})	4		A
E _{AS}	Single pulse avalanche energy (starting T _J = 25 °C, I _D =I _{AS} , V _{DD} = 50 V)	148		mJ
V _{iso}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; T _C =25 °C)		2500	V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5		V/ns
dv/dt ⁽⁴⁾	MOSFET dv/dt ruggedness	50		V/ns
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 150		°C

- Limited by package.
- Pulse width limited by safe operating area.
- I_{SD} ≤ 12 A, di/dt ≤ 100 A/μs, V_{Peak} ≤ V_{(BR)DSS}
- V_{DS} ≤ 640 V

Table 3. Thermal data

Symbol	Parameter	Value			Unit
		D ² PAK	TO-220	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	0.66		3.57	°C/W
R _{thj-amb}	Thermal resistance junction-amb max		62.5		
R _{thj-pcb} ⁽¹⁾	Thermal resistance junction-pcb max	30			

- When mounted on 1inch² FR-4 board, 2 oz Cu.

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 800\text{ V}$ $V_{DS} = 800\text{ V}, T_C = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$		0.37	0.45	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	870	-	pF
C_{oss}	Output capacitance		-	50	-	pF
C_{rss}	Reverse transfer capacitance		-	2	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{GS} = 0, V_{DS} = 0\text{ to }640\text{ V}$	-	110	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	43	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0$	-	5	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}, I_D = 12\text{ A}$ $V_{GS} = 10\text{ V}$ (see Figure 20)	-	29	-	nC
Q_{gs}	Gate-source charge		-	7		nC
Q_{gd}	Gate-drain charge		-	18		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 6\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 22)	-	16	-	ns
t_r	Rise time		-	16	-	ns
$t_{d(off)}$	Turn-off delay time		-	42	-	ns
t_f	Fall time		-	16	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		14	A
I_{SDM}	Source-drain current (pulsed)		-		56	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 12\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, (see Figure 21)	-	406		ns
Q_{rr}	Reverse recovery charge		-	5.7		μC
I_{RRM}	Reverse recovery current		-	28		A
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 21)	-	600		ns
Q_{rr}	Reverse recovery charge		-	7.9		μC
I_{RRM}	Reverse recovery current		-	26		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0$	30	-	-	V

The built-in back-to-back Zener diodes have been specifically designed to enhance not only the device's ESD capability, but also to make them capable of safely absorbing any voltage transients that may occasionally be applied from gate to source. In this respect, the Zener voltage is appropriate to achieve efficient and cost-effective protection of device integrity. The integrated Zener diodes thus eliminate the need for external components.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D²PAK

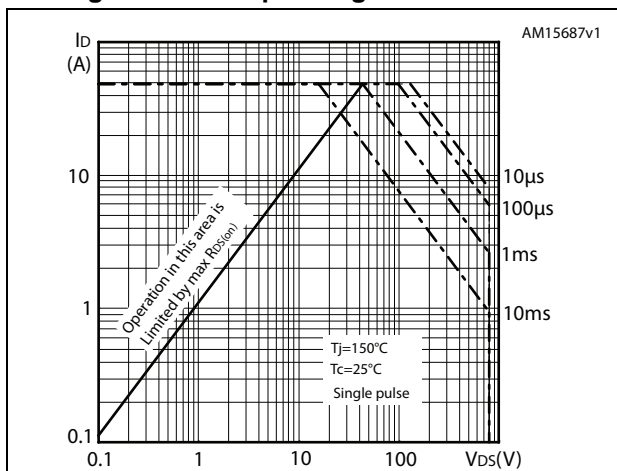


Figure 3. Thermal impedance for D²PAK

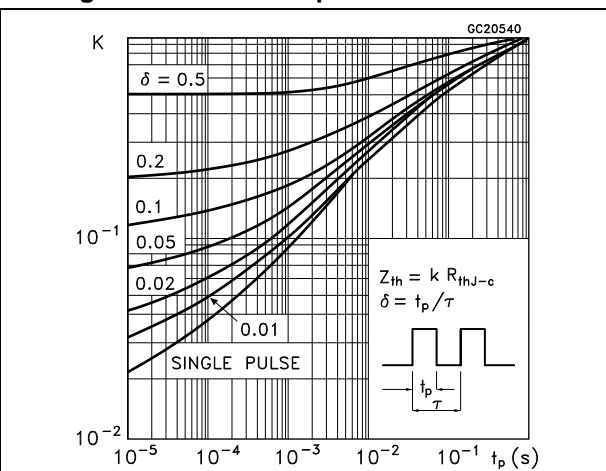


Figure 4. Safe operating area for TO-220FP

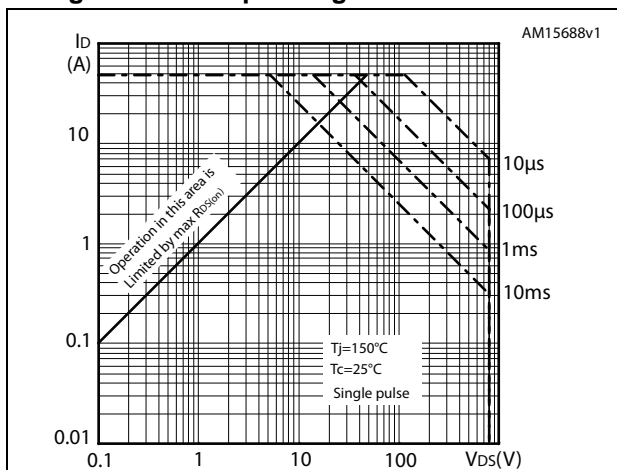


Figure 5. Thermal impedance for TO-220FP

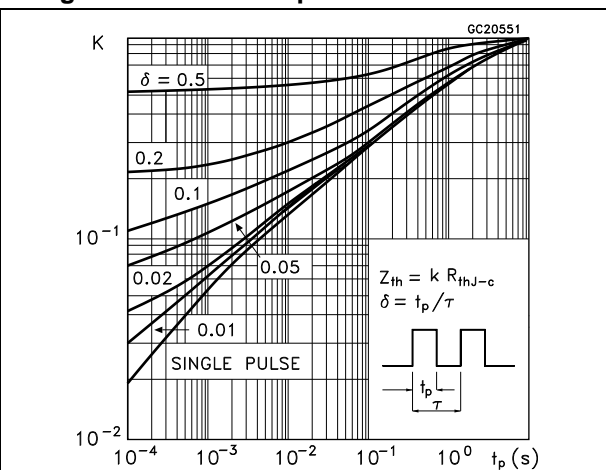


Figure 6. Safe operating area for TO-220

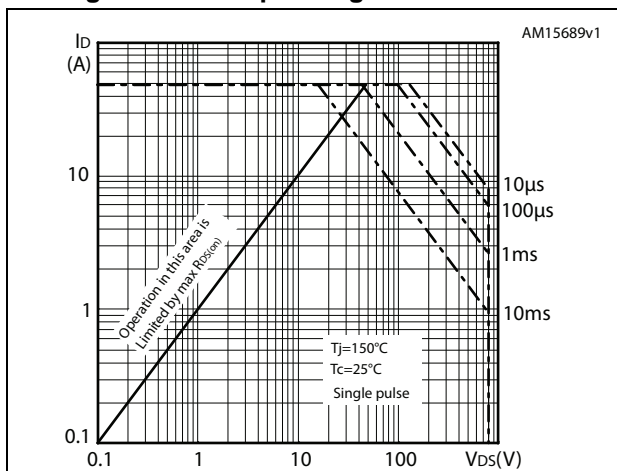


Figure 7. Thermal impedance for TO-220

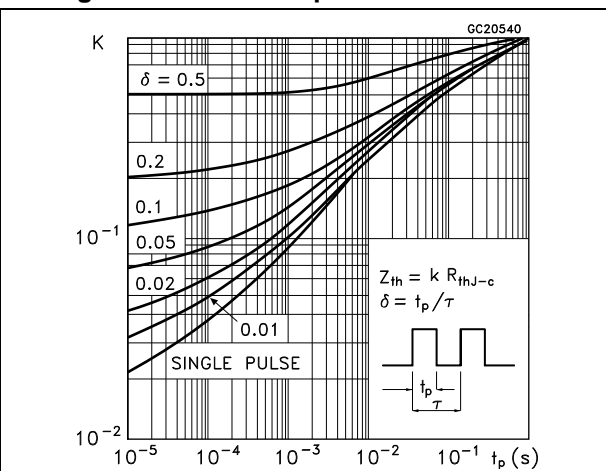


Figure 8. Output characteristics

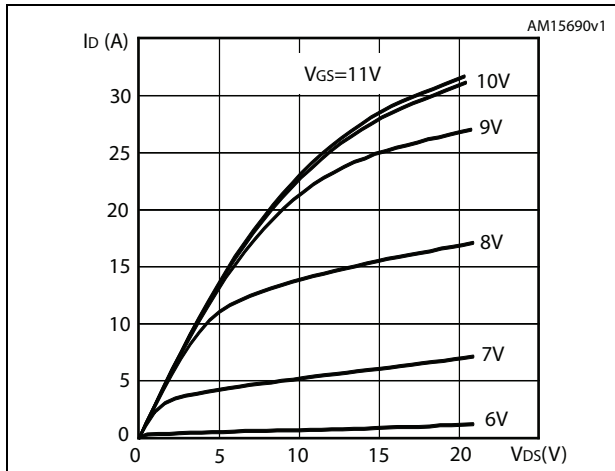


Figure 9. Transfer characteristics

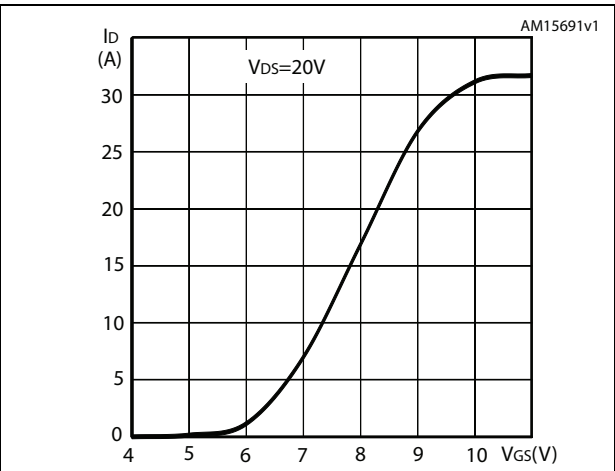


Figure 10. Normalized $B_{V_{DS}}$ vs temperature

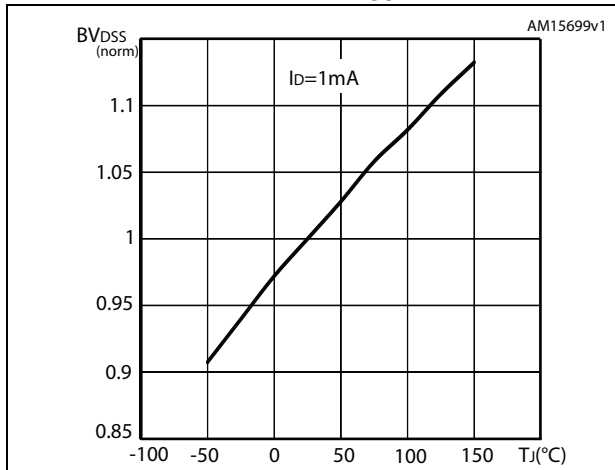


Figure 11. Static drain-source on-resistance

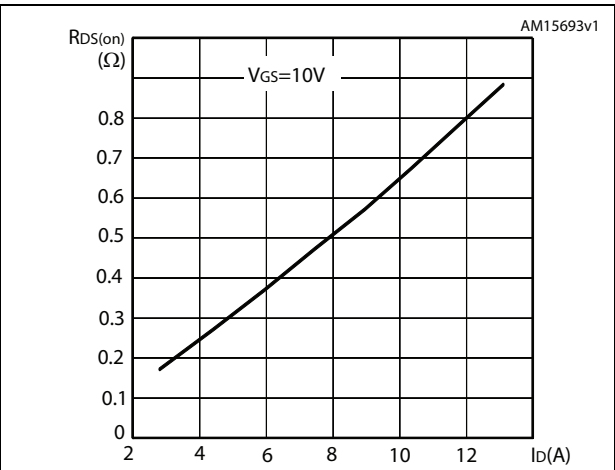


Figure 12. Gate charge vs gate-source voltage

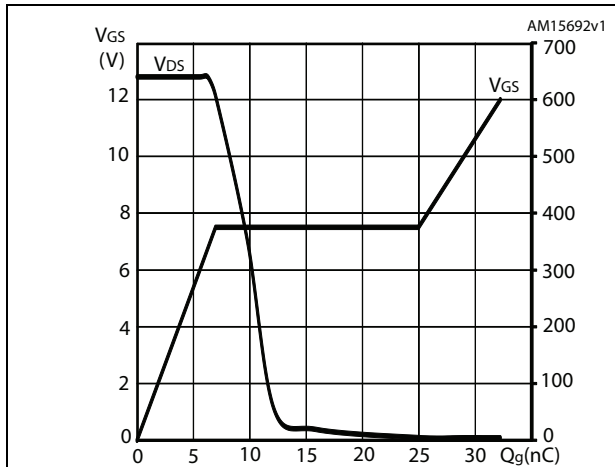


Figure 13. Capacitance variations

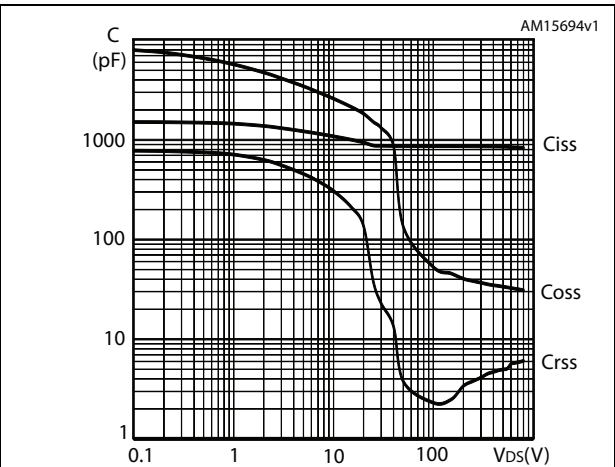


Figure 14. Normalized gate threshold voltage vs temperature

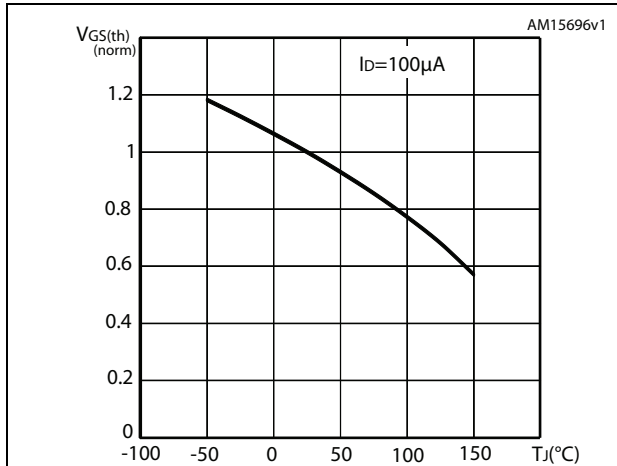


Figure 15. Normalized on-resistance vs temperature

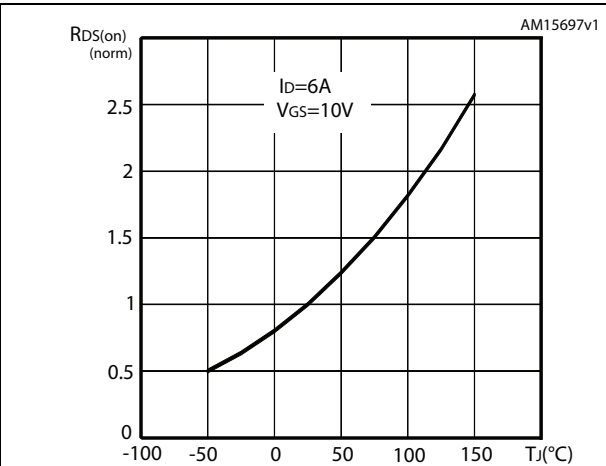


Figure 16. Source-drain diode forward characteristics

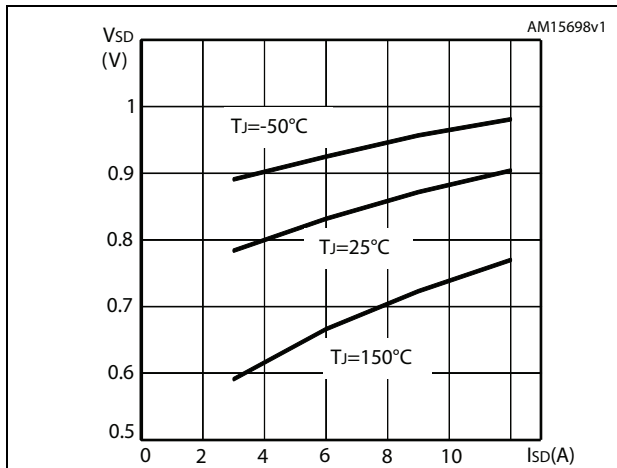


Figure 17. Output capacitance stored energy

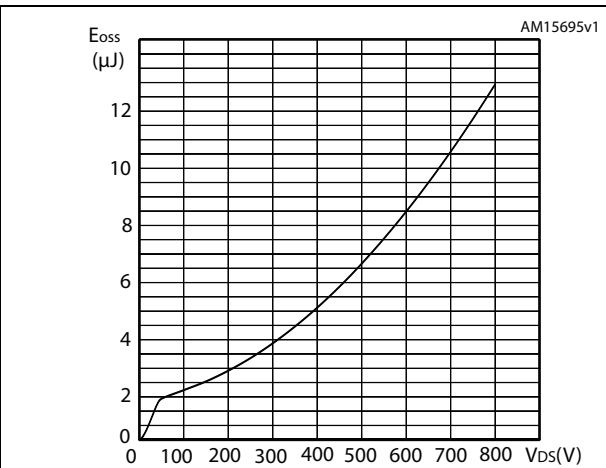
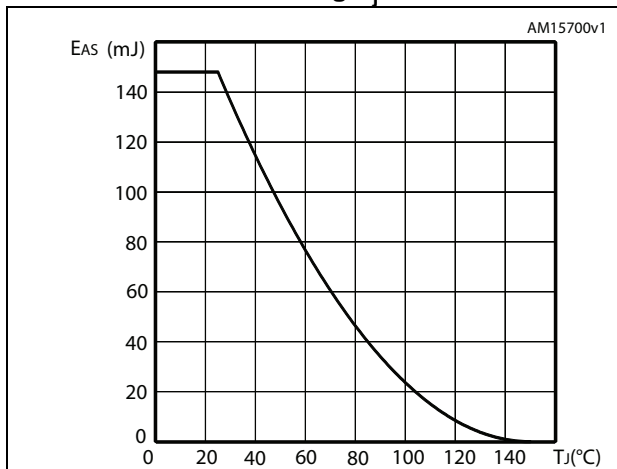


Figure 18. Maximum avalanche energy vs. starting T_j



3 Test circuits

Figure 19. Switching times test circuit for resistive load



Figure 20. Gate charge test circuit



Figure 21. Test circuit for inductive load switching and diode recovery times

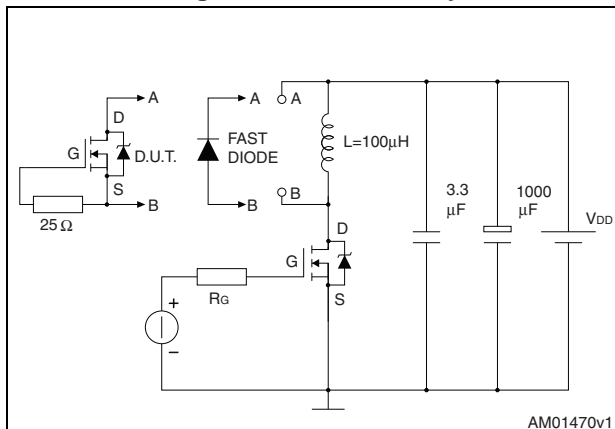


Figure 22. Unclamped inductive load test circuit

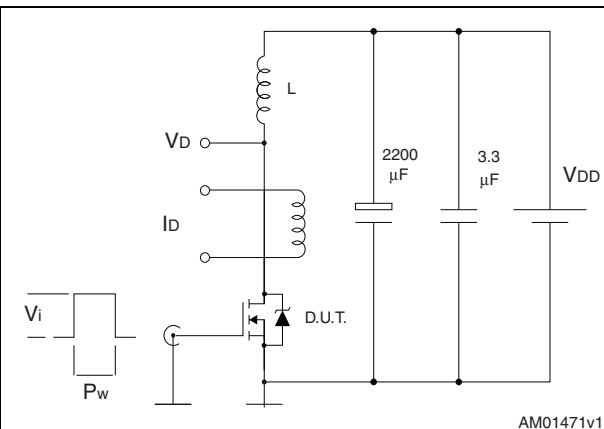


Figure 23. Unclamped inductive waveform



Figure 24. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK (TO-263) drawing

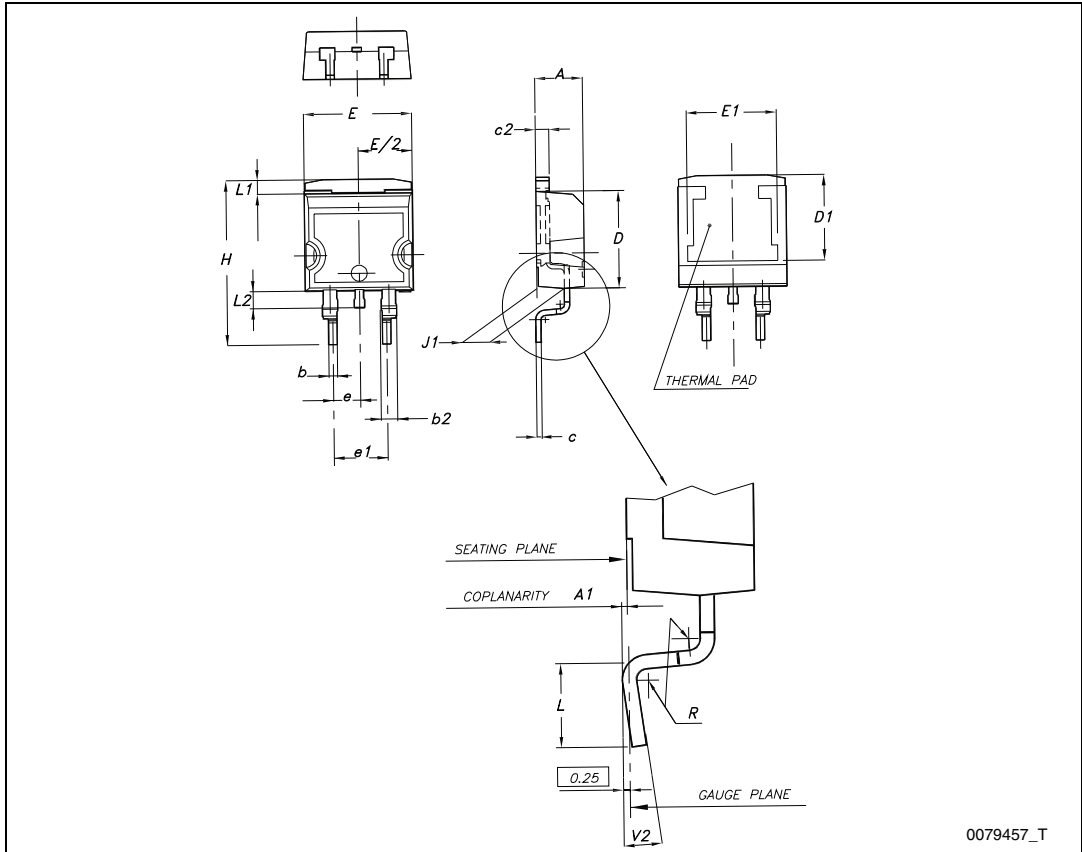
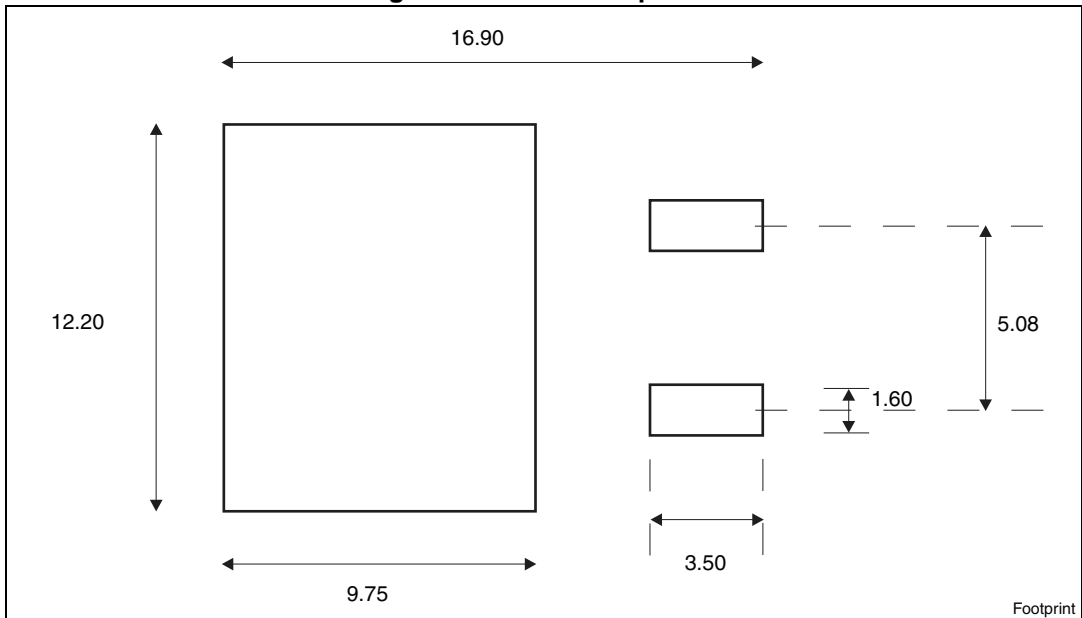


Figure 26. D²PAK footprint^(a)

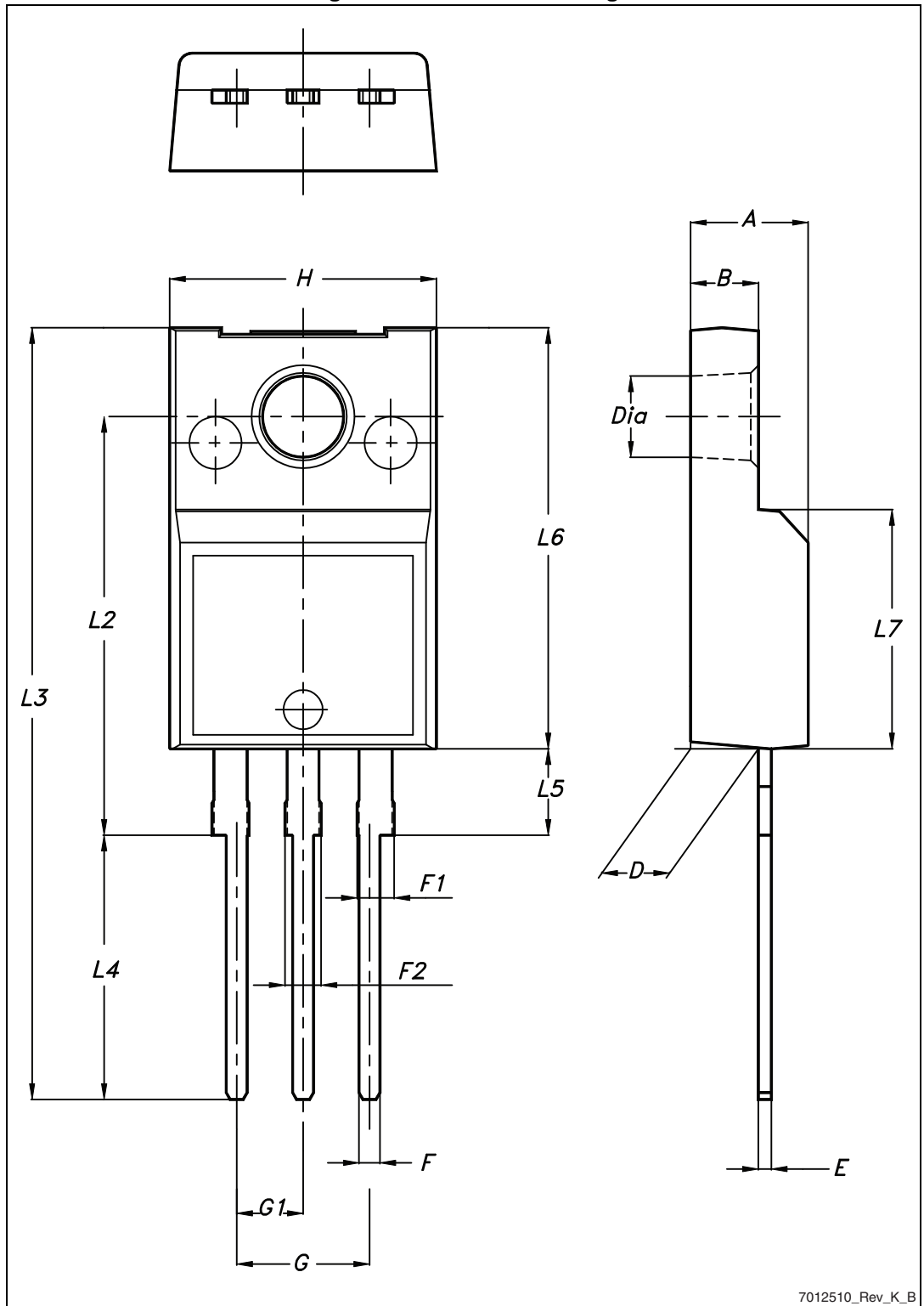


a. All dimension are in millimeters

Table 10. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 27. TO-220FP drawing

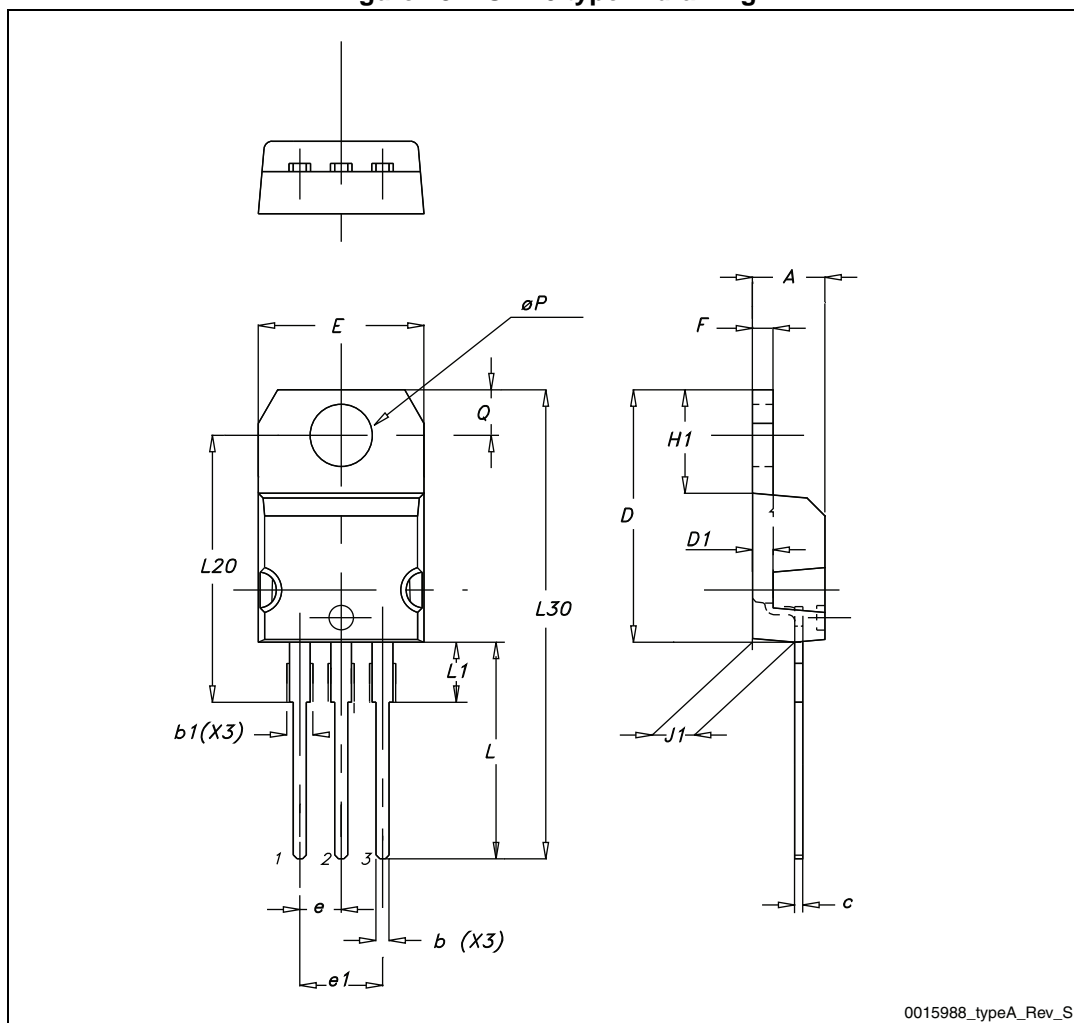


7012510_Rev_K_B

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 28. TO-220 type A drawing



5 Packaging mechanical data

Table 12. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape

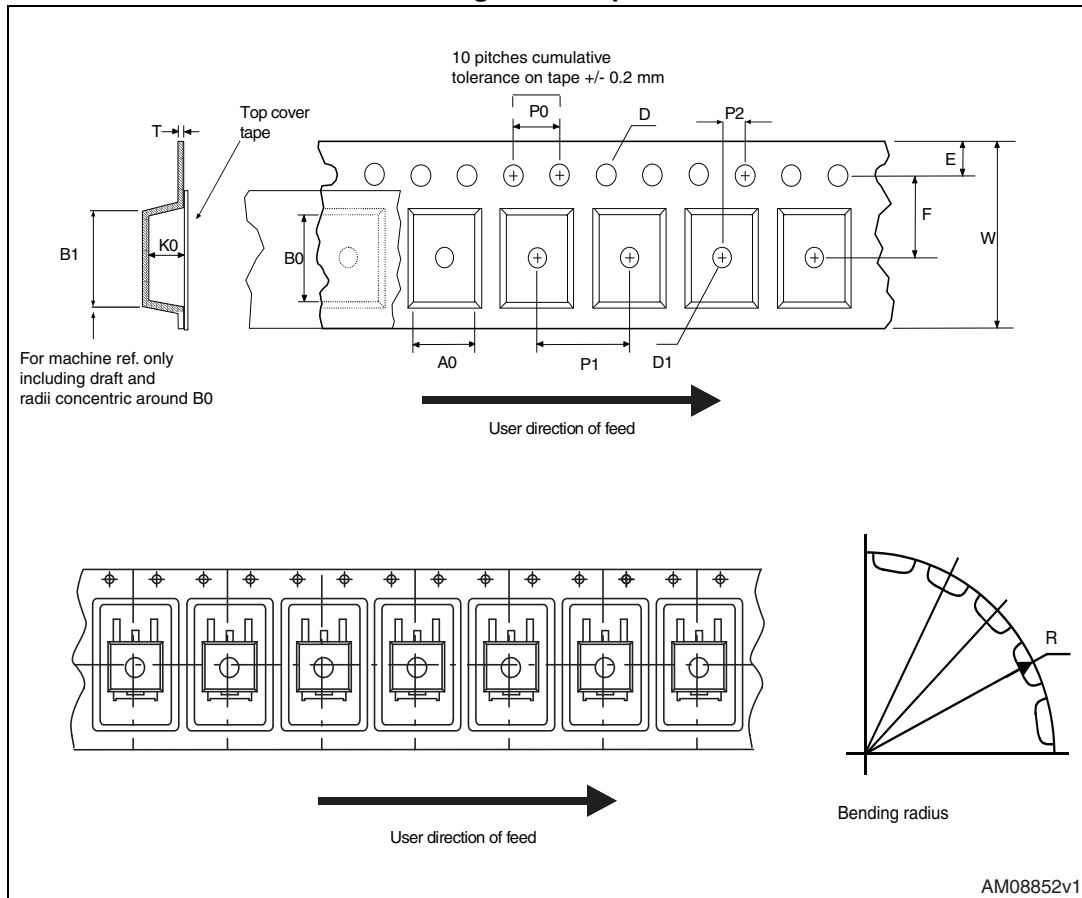
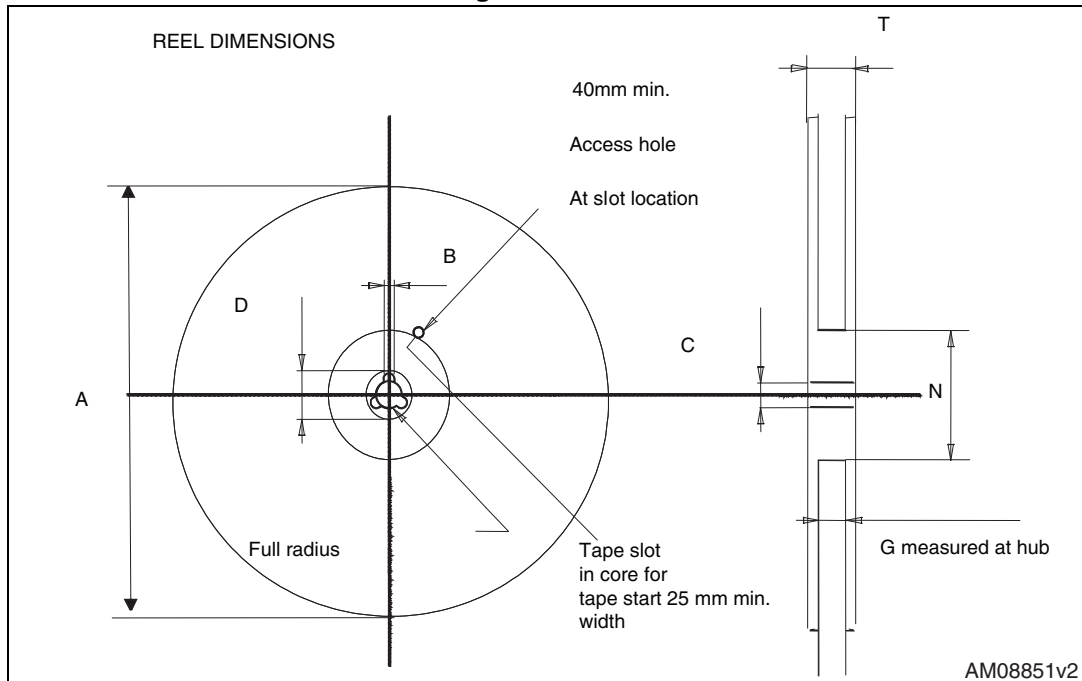


Figure 30. Reel



6 Revision history

Table 13. Document revision history

Date	Revision	Changes
07-Mar-2013	1	Initial release.
27-Mar-2013	2	Updated Figure 1: Internal schematic diagram . Minor text changes. Document status promoted from preliminary data to production data.
15-Apr-2013	3	– Modified: E_{AS} value, the entire typical values on Table 5, 6 and 7 – Inserted: Section 2.1: Electrical characteristics (curves) – Minor text changes

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